

INFORMATION DISCLOSURE
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APPLICANT

NAKAMURA et al

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May 1, 2000

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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>[Signature]</i>	6,172,382	01/2001	NAGAHAMA et al.			

FOREIGN PATENT DOCUMENTS

DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
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OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

<i>[Signature]</i>	NAKAMURA et al., "Present Status of InGaN/GaN/AlGaIn-Based Laser Diodes," Proceedings of the Second International Conference on Nitride Semiconductors (INCS '97), 1997, pp. 444-446
<i>[Signature]</i>	SHIBATA et al., "Hybride Vapor Phase Epitaxy Growth of High Quality GaN Bulk Single Crystal by Epitaxial Lateral Overgrowth," Proceedings of the Second International Conference on Nitride Semiconductors (INCS '97), Oct. 27-31, 1997, pp. 154-155
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<i>[Signature]</i>	NAKAMURA et al., "InGaN-Based Multi-Quantum-Well-Structure Laser Diodes," Jpn. J. Appl. Phys., Vol. 35, Part 2, No. 1B (Jan. 15, 1996), pp. L74-L76
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<i>[Signature]</i>	NAKAMURA et al., "Room-temperature continuous-wave operation of InGaN multi-quantum-well structure laser diodes," Appl. Phys. Lett. 69(26) (Dec. 23, 1996), pp. 4056-4058

*Examiner

Date Considered

5/06

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